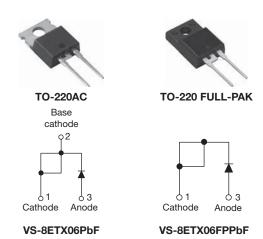


Vishay Semiconductors

# Hyperfast Rectifier, 8 A FRED Pt®

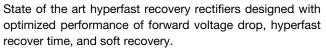


PRODUCT SUMMARY					
Package	TO-220AC, TO-220FP				
I <sub>F(AV)</sub>	8 A				
$V_{R}$	600 V				
V <sub>F</sub> at I <sub>F</sub>	3.0 V				
t <sub>rr</sub> (typ.)	15 ns				
T <sub>J</sub> max.	175 °C				
Diode variation	Single die				

### **FEATURES**

- · Hyperfast recovery time
- Benchmark ultralow forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

### **DESCRIPTION/APPLICATIONS**



The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Repetitive peak reverse voltage	$V_{RRM}$		600	V		
Average restified forward current	1	T <sub>C</sub> = 143 °C	- 8			
Average rectified forward current FULL-PAK	I <sub>F(AV)</sub>	T <sub>C</sub> = 106 °C		^		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	110	Α		
Repetitive peak forward current	I <sub>FM</sub>		18			
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	600	-	-	Š	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A	-	2.3	3.0	V	
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.4	1.7		
Reverse leakage current I <sub>R</sub>		$V_R = V_R$ rated	-	0.3	50		
		$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	35	500	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	17	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ	

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# VS-8ETX06PbF, VS-8ETX06FPPbF

#### Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	15	19		
Reverse recovery time		I <sub>F</sub> = 8 A, dI <sub>F</sub> /dt = 100	A/ $\mu$ s, V <sub>R</sub> = 30 V	-	16	24	ne	
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	17	-	ns	
		T <sub>J</sub> = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 390 \text{ V}$	-	40	-		
Dook roopyon/ ourront	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.3	-	А	
Peak recovery current		T <sub>J</sub> = 125 °C		-	4.5	-		
Povorco rocovony oborgo	0	T <sub>J</sub> = 25 °C		-	20	-	nC	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	100	-	110	
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 600 A/µs	-	31	-	ns	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	12	-	А	
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	195	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDTIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	l l. leta		- 65	-	175	°C	
Thermal resistance,	D		-	1.4	2		
junction to case (FULL-PAK)	$R_{thJC}$		-	3.4	4.3		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0		12	kgf · cm	
Modifiling torque			(5.0)	_	(10)	(lbf · in)	
Marking device		Case style TO-220AC	8ETX06		X06		
ivial Killy device		Case style TO-220 FULL-PAK	8ETX06FP				

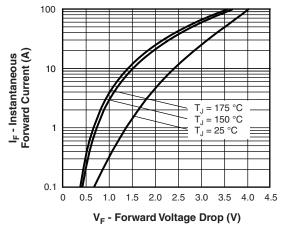


Fig. 1 - Typical Forward Voltage Drop Characteristics

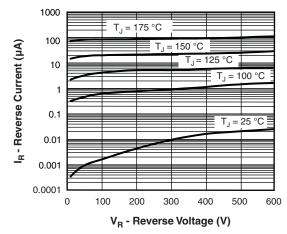


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



# Hyperfast Rectifier, 8 A FRED Pt® Vishay Semiconductors

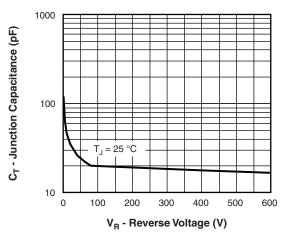


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

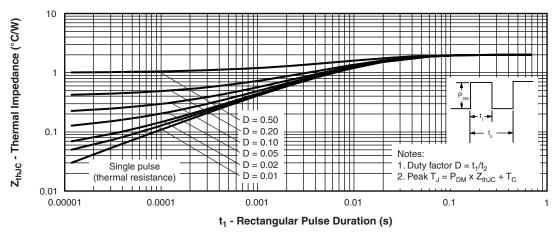


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

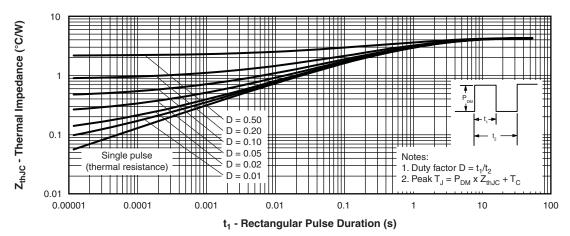


Fig. 5 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (FULL-PAK)

## VS-8ETX06PbF, VS-8ETX06FPPbF

## Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



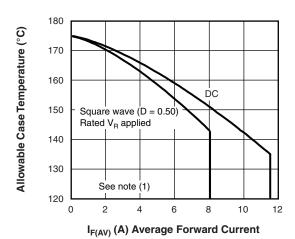


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current

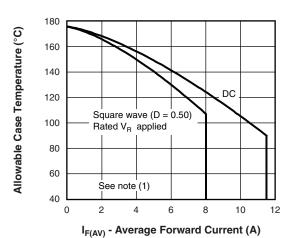


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

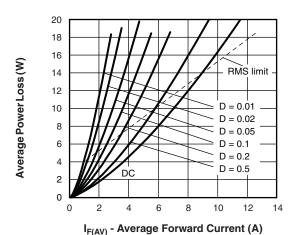


Fig. 8 - Forward Power Loss Characteristics

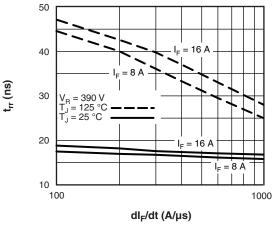


Fig. 9 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

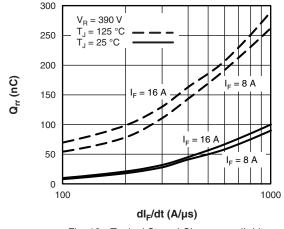


Fig. 10 - Typical Stored Charge vs.  $dI_F/dt$ 

#### Note

(1) Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>thJC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 8); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = Rated V<sub>R</sub>



## Hyperfast Rectifier, 8 A FRED Pt®

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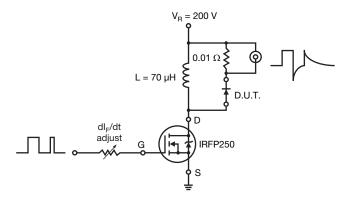
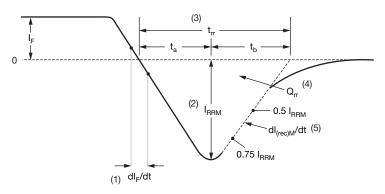


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$ and  $I_{\text{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

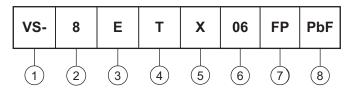
# VS-8ETX06PbF, VS-8ETX06FPPbF

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



### **ORDERING INFORMATION TABLE**

Device code



Vishay Semiconductors product

Current rating (8 = 8 A)

E = Single diode

T = TO-220, DPAK

X = Hyperfast rectifier

Voltage rating (06 = 600 V)

• None = TO-220AC

• FP = TO-220 FULL-PAK

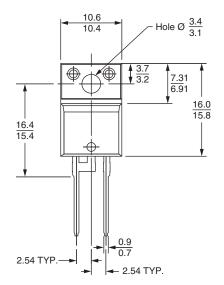
8 PbF = Lead (Pb)-free

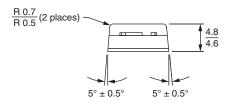
Tube standard pack quantity: 50 pieces

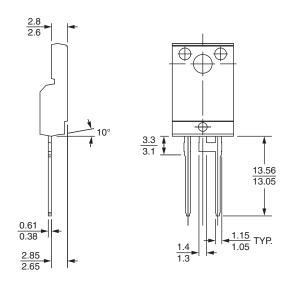
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-220AC	www.vishay.com/doc?95221			
Differsions	TO-220AC FULL-PAK	www.vishay.com/doc?95005			
Part marking information	TO-220AC	www.vishay.com/doc?95224			
	TO-220AC FULL-PAK	www.vishay.com/doc?95009			
SPICE model		www.vishay.com/doc?95393			

## Vishay Semiconductors

### **DIMENSIONS** in millimeters







#### Lead assignments

Diodes

1 + 2 - Cathode

3 - Anode

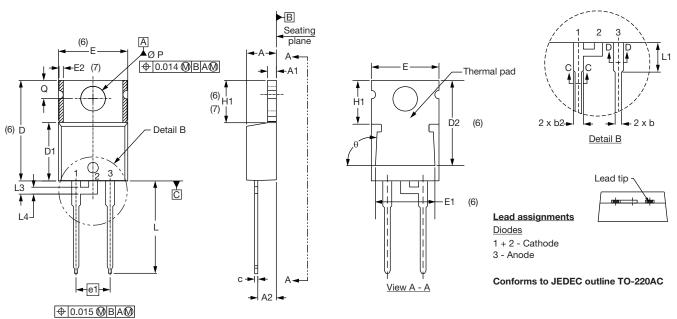
Conforms to JEDEC outline TO-220 FULL-PAK



## Vishay Semiconductors

### **TO-220AC**

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.25	4.65	0.167	0.183		
A1	1.14	1.40	0.045	0.055		
A2	2.56	2.92	0.101	0.115		
b	0.69	1.01	0.027	0.040		
b1	0.38	0.97	0.015	0.038	4	
b2	1.20	1.73	0.047	0.068		
b3	1.14	1.73	0.045	0.068	4	
С	0.36	0.61	0.014	0.024		
c1	0.36	0.56	0.014	0.022	4	
D	14.85	15.25	0.585	0.600	3	
D1	8.38	9.02	0.330	0.355		
D2	11.68	12.88	0.460	0.507	6	
Е	10.11	10.51	0.398	0.414	3, 6	

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		
		•		•	•

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline





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